

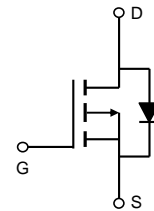
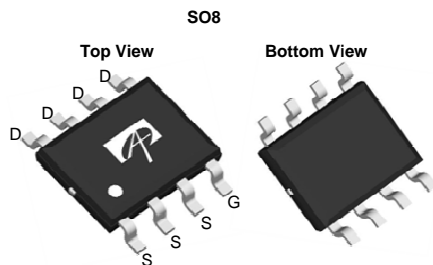
### General Description

The AO4421 combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is ideal for load switch and battery protection applications.

### Product Summary

$V_{DS}$	-60V
$I_D$ (at $V_{GS}=-10V$ )	-6.2A
$R_{DS(ON)}$ (at $V_{GS}=-10V$ )	< 40m $\Omega$
$R_{DS(ON)}$ (at $V_{GS} = -4.5V$ )	< 50m $\Omega$

100% UIS Tested  
 100%  $R_g$  Tested



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ\text{C}$	-6.2
		$T_A=70^\circ\text{C}$	-5
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-40	A
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10\text{s}$	$R_{\theta JA}$	24	40	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient <sup>A</sup>	Steady-State		54	75	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{\theta JL}$	21	30	$^\circ\text{C}/\text{W}$

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-48V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA	-1	-2	-3	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-5V	-40			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6.2A T <sub>J</sub> =125°C		32 53	40 70	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A		40	50	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-6.2A		18		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.74	-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-4.2	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-30V, f=1MHz		2417	2900	pF
C <sub>oss</sub>	Output Capacitance			179		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			120		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		1.9	2.3	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(10V)</sub>	Total Gate Charge (10V)	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-30V, I <sub>D</sub> =-6.2A		46.5	55	nC
Q <sub>g(4.5V)</sub>	Total Gate Charge (4.5V)			22.7		nC
Q <sub>gs</sub>	Gate Source Charge			9.1		nC
Q <sub>gd</sub>	Gate Drain Charge			9.2		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-30V, R <sub>L</sub> =4.7Ω, R <sub>GEN</sub> =3Ω		9.8		ns
t <sub>r</sub>	Turn-On Rise Time			6.1		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			44		ns
t <sub>f</sub>	Turn-Off Fall Time			12.7		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-6.2A, dI/dt=100A/μs		34	42	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-6.2A, dI/dt=100A/μs		47		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

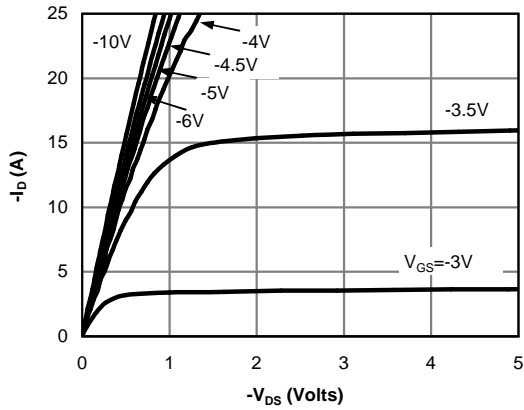


Fig 1: On-Region Characteristics

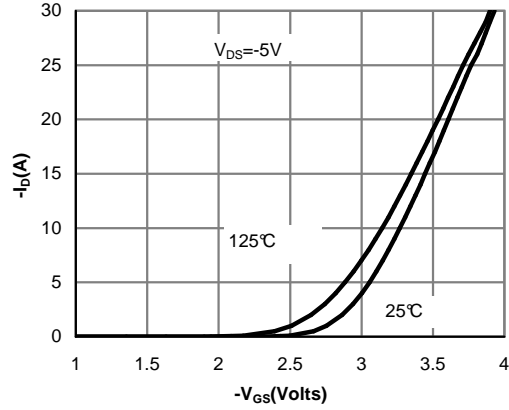


Figure 2: Transfer Characteristics

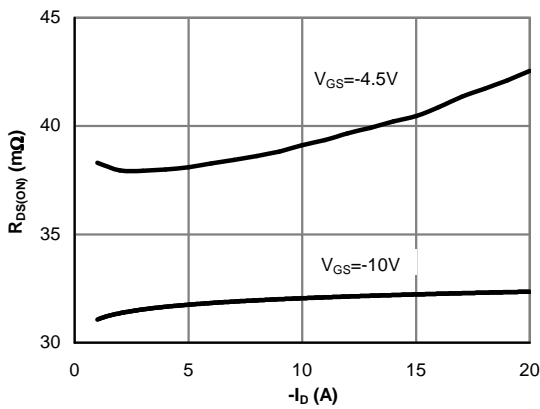


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

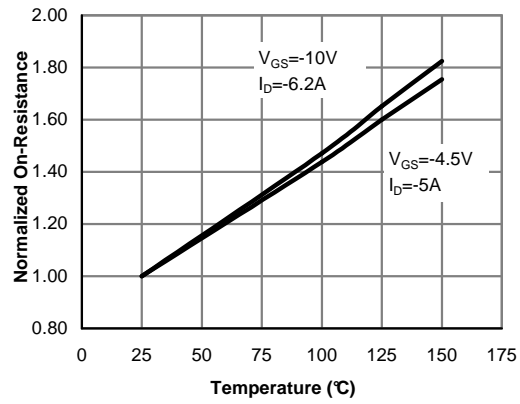


Figure 4: On-Resistance vs. Junction Temperature

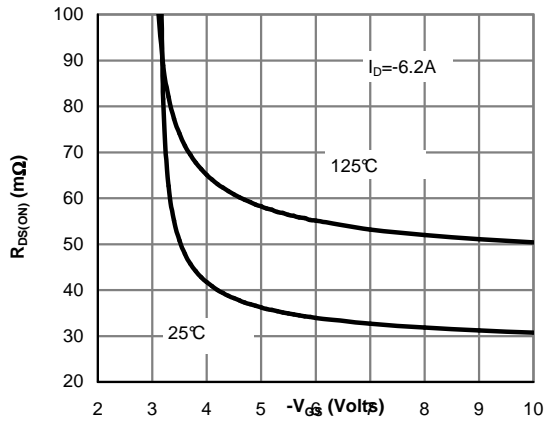


Figure 5: On-Resistance vs. Gate-Source Voltage

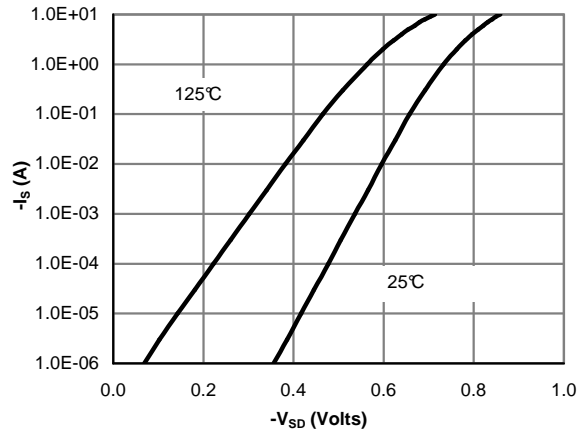


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

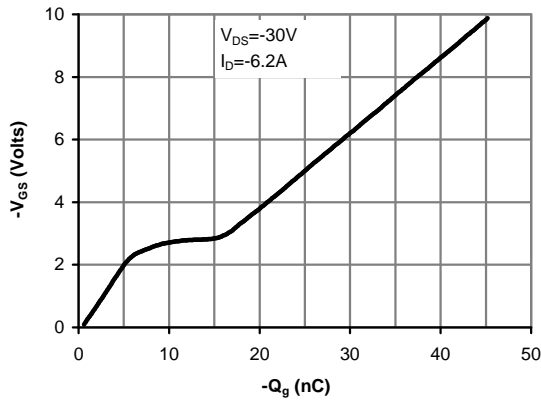


Figure 7: Gate-Charge Characteristics

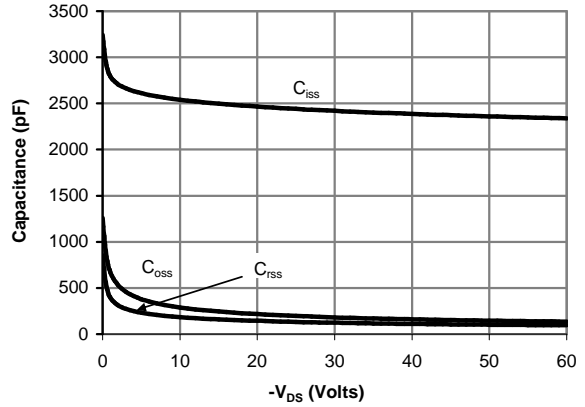


Figure 8: Capacitance Characteristics

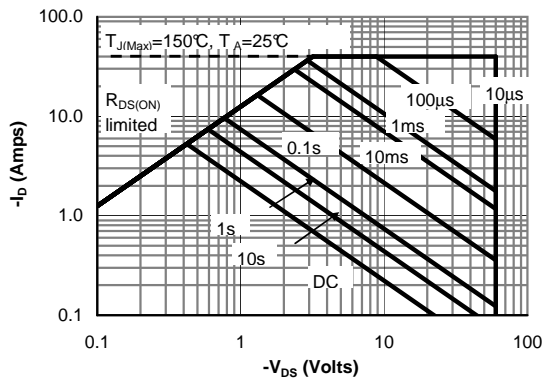


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

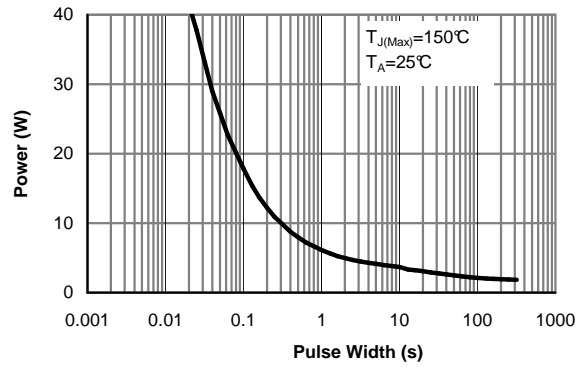


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

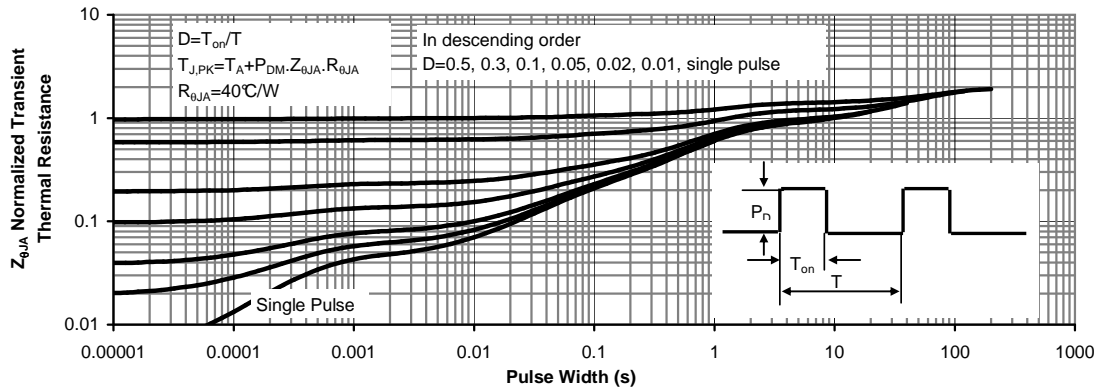


Figure 11: Normalized Maximum Transient Thermal Impedance